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John L. Sturtevant
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Contents

vii	<i>Conference Committee</i>
ix	<i>Introduction</i>

KEYNOTE SESSION

- 8327 03 **Implications of triple patterning for 14nm node design and patterning (Keynote Paper)** [8327-02]
K. Lucas, Synopsys, Inc. (United States); C. Cork, Synopsys, Inc. (France); B. Yu, Univ. of Texas (United States); G. Luk-Pat, B. Painter, Synopsys, Inc. (United States); D. Z. Pan, The Univ. of Texas at Austin (United States)
- 8327 04 **Yield enhancement with DFM (Keynote Paper)** [8327-03]
S. W. Paek, J. H. Kang, N. Ha, B.-M. Kim, D. H. Jang, J. Jeon, D. Kim, K. Y. Chung, S. Yu, J. H. Park, S. Bae, D. Song, W. Noh, Y. Kim, H. Song, H. Choi, K. S. Kim, K.-M. Choi, W. Choi, J. Jeon, J. Lee, K.-S. Kim, S. Park, N.-Y. Chung, K. Lee, Y. Hong, B. Kim, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)

DFDP: DESIGN FOR DOUBLE PATTERNING

- 8327 05 **Layout optimization through robust pattern learning and prediction in SADP gridded designs** [8327-04]
J.-Y. Wu, Univ. of California, Santa Barbara (United States); M. Simmons, Mentor Graphics Corp. (United States); M. Marek-Sadowska, Univ. of California, Santa Barbara (United States)
- 8327 06 **Self-aligned double patterning (SADP) compliant design flow** [8327-05]
Y. Ma, GLOBALFOUNDRIES Inc. (United States); J. Sweis, Cadence Design Systems, Inc. (United States); H. Yoshida, Y. Wang, J. Kye, H. J. Levinson, GLOBALFOUNDRIES Inc. (United States)
- 8327 07 **Design friendly double patterning** [8327-06]
E. Yesilada, STMicroelectronics (France)
- 8327 08 **Pattern matching for double patterning technology-compliant physical design flows** [8327-07]
L. T.-N. Wang, V. Dai, L. Capodiecici, GLOBALFOUNDRIES Inc. (United States)

DESIGN RULES AND ROUTING

- 8327 09 **Design-of-experiments based design rule optimization** [8327-08]
A. A. Kagalwalla, Univ. of California, Los Angeles (United States); S. Muddu, L. Capodiecici, GLOBALFOUNDRIES Inc. (United States); C. Zelnik, Sagantec Inc. (United States); P. Gupta, Univ. of California, Los Angeles (United States)

- 8327 0A **Fully integrated litho aware PnR design solution** [8327-09]
C. Beylier, STMicroelectronics (France); C. Moyroud, Mentor Graphics Corp. (France);
F. Bernard Granger, F. Robert, E. Yesilada, Y. Trouiller, J.-C. Marin, STMicroelectronics
(France)
- 8327 0B **Replacing design rules in the VLSI design cycle** [8327-10]
P. Hurley, K. Kryszczuk, IBM Zürich Research Lab. (Switzerland)
- 8327 0C **Smart double-cut via insertion flow with dynamic design-rules compliance for fast new technology adoption** [8327-11]
A. Abdulghany, R. Fathy, Mentor Graphics Corp. (United States); L. Capodiecici, P. Pathak,
S. Madhavan, S. Malik, GLOBALFOUNDRIES Inc. (United States)
- 8327 0D **Local loops for robust inter-layer routing at sub-20 nm nodes** [8327-12]
W. Huang, D. Morris, Carnegie Mellon Univ. (United States); N. Lafferty, L. Liebmann, IBM
Corp. (United States); K. Vaidyanathan, Carnegie Mellon Univ. (United States); K. Lai, IBM
Corp. (United States); L. Pileggi, A. J. Strojwas, Carnegie Mellon Univ. (United States)

DESIGN IMPLEMENTATION AND VARIABILITY

- 8327 0E **A primer of physical design for lithographers (Invited Paper)** [8327-13]
C.-M. Yuan, Freescale Semiconductor, Inc. (United States)
- 8327 0F **Analysis, quantification, and mitigation of electrical variability due to layout dependent effects in SOC designs** [8327-14]
Y. Wang, M. Zwolinski, Univ. of Southampton (United Kingdom); A. Appleby, M. Scoones,
S. Caldwell, T. Azam, Cambridge Silicon Radio Ltd. (United Kingdom); P. Hurat, Cadence
Design Systems, Inc. (United States); C. Pitchford, Cadence Design Systems, Inc. (United
Kingdom)
- 8327 0H **Design level variability analysis and parametric yield improvement methodology** [8327-16]
R. März, M. Keck, Intel GmbH (Germany)
- 8327 0I **Analysis of layout-dependent context effects on timing and leakage in 28nm** [8327-17]
P. McGuinness, Fastada (United States); P. Sharma, Freescale Semiconductor, Inc. (United
States); P. Hurat, Cadence Design Systems, Inc. (United States)
- 8327 0J **Variability aware compact model characterization for statistical circuit design optimization**
[8327-18]
Y. Qiao, K. Qian, C. J. Spanos, Univ. of California, Berkeley (United States)

JOINT SESSION WITH CONFERENCE 8326

- 8327 0K **Design and manufacturability tradeoffs in unidirectional and bidirectional standard cell layouts in 14nm node** [8327-19]
K. Vaidyanathan, S. H. Ng, D. Morris, Carnegie Mellon Univ. (United States); N. Lafferty,
L. Liebmann, IBM Corp. (United States); M. Bender, W. Huang, Carnegie Mellon Univ. (United
States); K. Lai, IBM Corp. (United States); L. Pileggi, A. Strojwas, Carnegie Mellon Univ. (United
States)

- 8327 0M **A novel methodology for triple/multiple-patterning layout decomposition** [8327-21]
R. S. Ghaida, Univ. of California, Los Angeles (United States); K. B. Agarwal, L. W. Liebmann,
S. R. Nassif, IBM Corp. (United States); P. Gupta, Univ. of California, Los Angeles (United
States)
- 8327 0N **Overlay, decomposition and synthesis methodology for hybrid self-aligned triple and
negative-tone double patterning** [8327-22]
W. Kang, Y. Chen, Peking Univ. (China)
- 8327 0O **Computational lithography work flows and design rule exploration automation** [8327-23]
S. Sethi, W. Stanton, K. Lucas, J. Hiserote, Synopsys, Inc. (United States); D. Hur, R. Choi,
SAMSUNG Electronics Co., Ltd. (Korea, Republic of)

SESSION 8 HOTSPOTS, CMP, AND FILL

- 8327 0P **Thickness-aware LFD for the hotspot detection induced by topology** [8327-24]
J.-H. Kang, N. Ha, J.-H. Park, B.-M. Kim, S. W. Paek, H. Choi, K. S. Kim, SAMSUNG Electronics
Co., Ltd. (Korea, Republic of); A. Mohy, S. Abdelwahed, M. Imam, Mentor Graphics
Consulting Division (Egypt)
- 8327 0Q **The complexity of fill at 28nm and beyond** [8327-25]
N. Rodriguez, J. Yang, Advanced Micro Devices, Inc. (United States); B. Graupp, J. Wilson,
E. Anikin, Mentor Graphics Corp. (United States)
- 8327 0S **In-design process hotspot repair using pattern matching** [8327-27]
D. Jang, N. Ha, J. Jeon, J.-H. Kang, S. W. Paek, H. Choi, K. S. Kim, SAMSUNG Electronics Co.,
Ltd. (Korea, Republic of); Y.-C. Lai, P. Hurat, W. Luo, Cadence Design Systems, Inc. (United
States)
- 8327 0T **Clean pattern matching for full chip verification** [8327-28]
S. Nakamura, Toshiba Corp. (Japan); T. Matsunawa, Toshiba Corp. R&D Ctr. (Japan);
C. Kodama, T. Urakami, N. Furuta, Toshiba Corp. (Japan); S. Kagaya, Toshiba
Microelectronics Corp. (Japan); S. Nojima, Toshiba Corp. R&D Ctr. (Japan); S. Miyamoto,
Toshiba Corp. (Japan)

POSTER SESSION

- 8327 0U **Framework for identifying recommended rules and DFM scoring model to improve
manufacturability of sub-20nm layout design** [8327-29]
P. Pathak, S. Madhavan, S. Malik, L. T.-N. Wang, L. Capodieci, GLOBALFOUNDRIES Inc.
(United States)
- 8327 0V **Self-aligned double and quadruple patterning layout principle** [8327-30]
K. Nakayama, C. Kodama, T. Kotani, Toshiba Corp. (Japan); S. Nojima, S. Mimotogi, Toshiba
Corp. R&D Ctr. (Japan); S. Miyamoto, Toshiba Corp. (Japan)
- 8327 0W **In-design hierarchical DFM closure for DFM-clean IP** [8327-31]
V. Tripathi, Freescale Semiconductor India (India); J. Subramanian, P. Sharma, Freescale
Semiconductor, Inc. (United States); K.-H. Chen, B. Kasthuri, P. Hurat, L. Layton, Cadence
Design Systems, Inc. (United States)

- 8327 0X **Automated yield enhancements implementation on full 28nm chip: challenges and statistics** [8327-32]
S. Malik, S. Madhavan, P. Pathak, L. Capodieci, GLOBALFOUNDRIES Inc. (United States); R. Fathy, A. Abdulghany, Mentor Graphics Corp. (United States)
- 8327 0Y **A study of pattern variability for device performance** [8327-33]
T.-H. Kim, D.-H. Han, A.-R. Hong, Y.-H. Kim, J.-S. Lee, Y.-H. Chu, K.-J. Lee, Y.-J. Park, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
- 8327 0Z **Intra-cell process variability and compact modeling of LWR effects: from self-aligned multiple patterning to multiple-gate MOSFETs** [8327-34]
Y. Chen, W. Kang, Q. Cheng, Peking Univ. (China)
- 8327 10 **Consideration of correlativity between litho and etching shape** [8327-35]
R. Matsuoka, H. Mito, Hitachi High-Technologies Corp. (Japan); S. Shinoda, Y. Toyoda, Hitachi Research Lab., Hitachi Ltd. (Japan)
- 8327 11 **Advanced techniques for design assembly and characterization for the 14nm node with LFD using a black box API** [8327-36]
J. Opitz, A. Torres, Mentor Graphics Corp. (United States); I. Graur, IBM Corp. (United States); W. Manhaway, S. Kanodia, Mentor Graphics Corp. (United States); M. Shafee, S. Mohamed, A. Hassand, Mentor Graphics Corp. (Egypt); J. Bickford, IBM Corp. (United States)
- 8327 14 **Fast optical proximity correction with timing optimization ready standard cells** [8327-39]
Y. Qu, C. H. Heng, A. Tay, T. H. Lee, National Univ. of Singapore (Singapore)
- 8327 15 **Electrical design for manufacturability and lithography and stress variability hotspot detection flows at 28nm** [8327-40]
P. Hurat, Cadence Design Systems, Inc. (United States); J. Zhu, E. Teoh, GLOBALFOUNDRIES Singapore (Singapore)
- 8327 16 **Yield impacting systematic defects search and management** [8327-41]
J. Zhang, Q. Xu, X. Zhang, X. Zhao, J. Ning, Semiconductor Manufacturing International Corp. (China); G. Cheng, S. Chen, G. Zhang, Anchor Semiconductor, Inc. (China); A. Vikram, B. Su, Anchor Semiconductor, Inc. (United States)
- 8327 17 **Model-based searching method to find the integrated critical failure on the wafer** [8327-43]
B.-S. Kang, N.-Y. Chung, H.-K. Park, S.-J. Lee, J.-H. Ku, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
- 8327 18 **A scoring methodology for quantitatively evaluating the quality of double patterning technology-compliant layouts** [8327-44]
L. T.-N. Wang, S. Madhavan, S. Malik, P. Pathak, L. Capodieci, GLOBALFOUNDRIES Inc. (United States)

Author Index

Conference Committee

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Chi-Min Yuan, Freescale Semiconductor, Inc. (United States)

Session Chairs

- 1 Keynote Session
Mark E. Mason, Texas Instruments Inc. (United States)
John L. Sturtevant, Mentor Graphics Corporation (United States)
- 2 DFDP: Design for Double Patterning
Lars W. Liebmann, IBM Corporation (United States)
Vivek K. Singh, Intel Corporation (United States)
- 3 Design Rules and Routing
Andrew R. Neureuther, University of California, Berkeley (United States)
Luigi Capodieci, GLOBALFOUNDRIES Inc. (United States)

- 4 Design Implementation and Variability
Rob Aitken, ARM Inc. (United States)
Michael L. Rieger, Synopsys, Inc. (United States)
- 5 Optical/DFM: Joint Session with Conference 8326
Mark E. Mason, Texas Instruments Inc. (United States)
Will Conley, Dynamic Intelligence (United States)
- 6 Joint Session with Conference 8326
John L. Sturtevant, Mentor Graphics Corporation (United States)
Kafai Lai, IBM Corporation (United States)
- 7 Hotspots, CMP, and Fill
Chul-Hong Park, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
Jason P. Cain, Advanced Micro Devices, Inc. (United States)

Introduction

I am very excited to be writing this introduction to the Proceedings of the 2012 SPIE conference on Design for Manufacturability through Design-Process Integration (DfM-DPI).

This marks the sixth year of the DfM-DPI conference, and I could not be happier with the quality of work that was submitted for publication this year. Experts from around the world participated representing various segments of the Semiconductor industry and academia. Once again, we enjoyed strong representation from Europe, Asia, and America. We even saw an increase in participation (as measured by paper submissions) over last year, indicating that the industry remains heavily focused on Design for Manufacturability.

Our keynote speakers this year were simply outstanding. Well recognized as premier experts in their field, the presenters addressed critical manufacturability issues facing us during the coming transition to EUV, complications inherent in triple patterning; and successful approaches to using DfM as part of an overall yield enhancement strategy.

The depth of the technical sessions was also impressive, covering a wide range of topics. Emphasis on double patterning implications was apparent this year, as you might expect given current industry trends. An invited tutorial presentation describing the design flow (tailored to lithographers) was particularly well received. Other topics of note included design rule implications, place and route impact to DfM and variability.

One highlight of the event was the joint session with the Optical Lithography conference. Recognizing the powerful overlap between computational lithography topics like OPC and SMO, two joint sessions were presented featuring papers of mutual interest to both conferences. The standing-room-only crowd is clear evidence that this sort of inter-conference collaboration should continue in the future. Special thanks to the Optical guys for making this happen.

The bottom line is that the conference was very successful by any measure. As a personal note, I would like to thank the authors and conference attendees for their active participation: this conference is for you, and you make it happen.

Of course none of this would be possible without the generous support (and patience) of my co-chair (John Sturtevant of Mentor Graphics) and SPIE staff. Further, I deeply appreciate the efforts of the conference program committee for all their help in putting the program together and chairing sessions.

Together with these excellent people, I am already working hard to put together an even better program for 2013. I cannot wait to see you there.

Mark E. Mason
John L. Sturtevant

